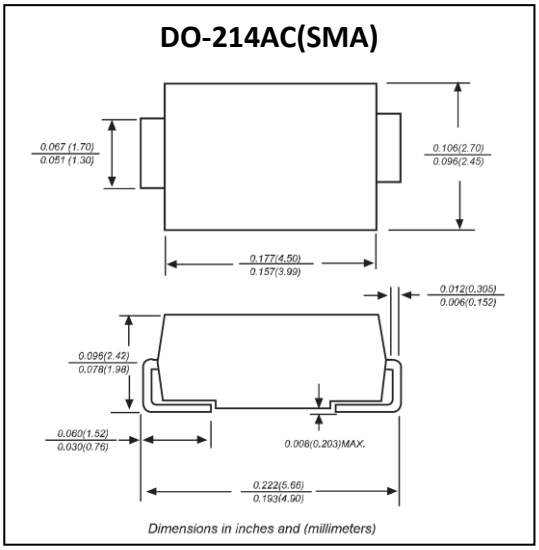
ES1A-ES1J

50~600V-1A Super Fast Recovery Rectifier Diode

ES1A-ES1J



Feature

- I_O 1A
- V_{RRM} 50V-600V
- Glass passivated chip
- High surge current capability

Application

- Rectifier

Marking

- ES1X X:From A To J

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	ES1								Unit
		A	B	C	D	E	G	H	J	
Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	350	420	V
Average Forward Current 60HZ Half-sine wave, Resistance load, T_L=120℃	$I_{F(AV)}$	1								A
Non-repetitive Peak Forward Surge Current 60Hz Half-sine wave ,1 cycle ,Ta =25℃	I_{FSM}	30								A
Junction Temperature	T_J	-55 ~ +150								℃
Storage Temperature	T_{STG}	-55 ~ +150								℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition		ES1								Unit
				A	B	C	D	E	G	H	J	
Peak Forward Voltage	V_F	I_F =1A		0.95				1.25			1.70	V
Maximum reverse recovery time	t_{rr}	I_F=0.5A,I_R=1.0A,I_{rr}= 0.25A		35								ns
Peak Reverse Current	I_{RRM1}	V_{RM}=V_R	T_a=25℃	5								uA
	I_{RRM2}	RM	T_a=100℃	100								uA
Thermal Resistance(Typical)	$R_{\theta J-A}$	Between junction and ambient		85								℃/W
	$R_{\theta J-L}$	Between junction and terminal		35								℃/W

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

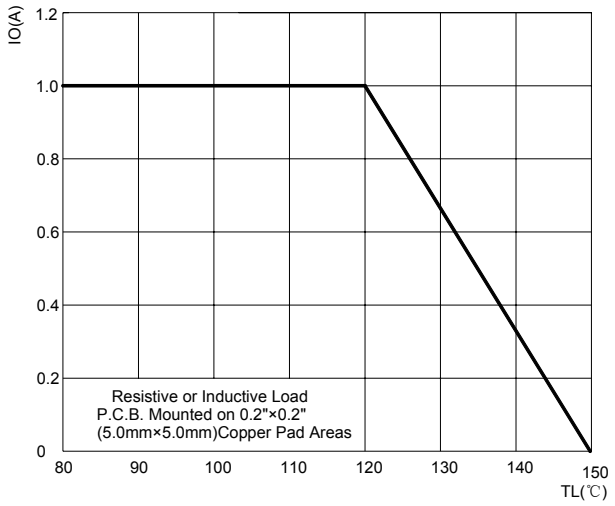


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

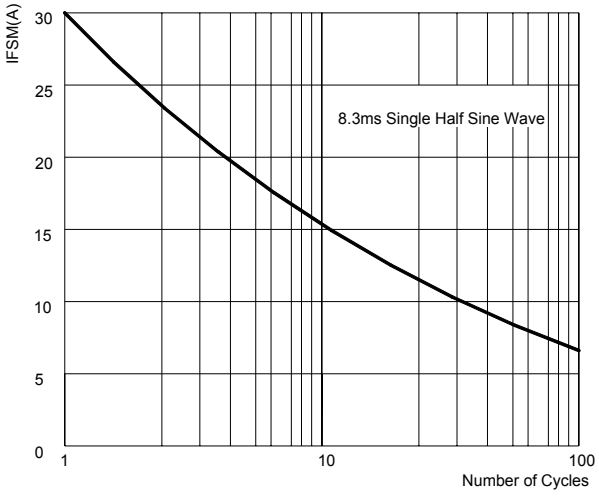


FIG.3: TYPICAL FORWARD CHARACTERISTICS

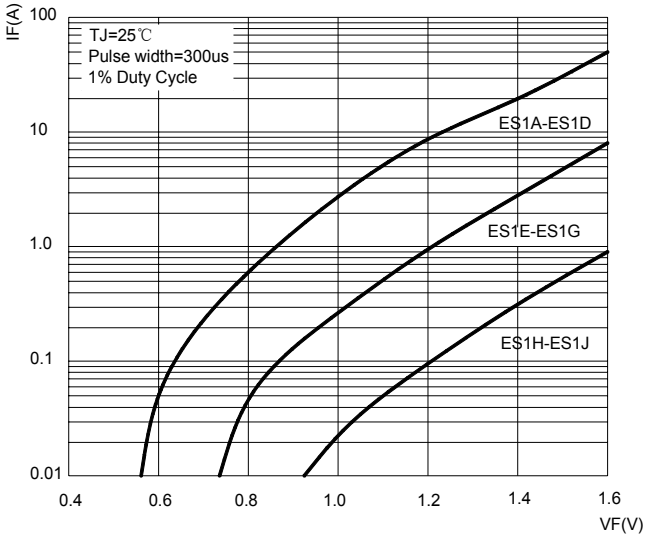
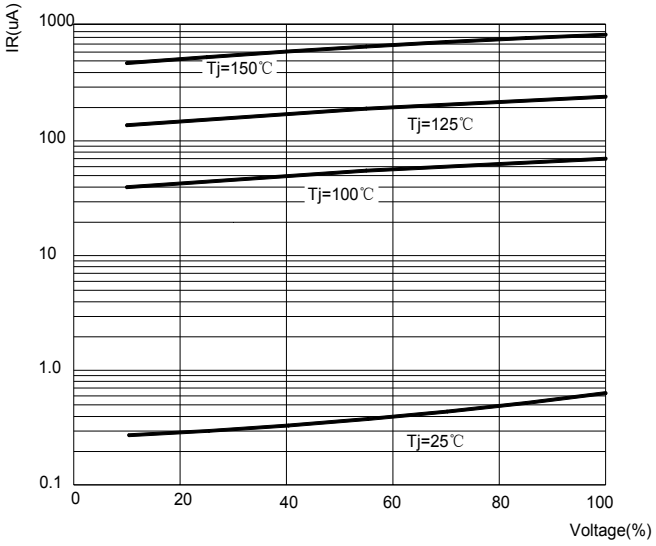
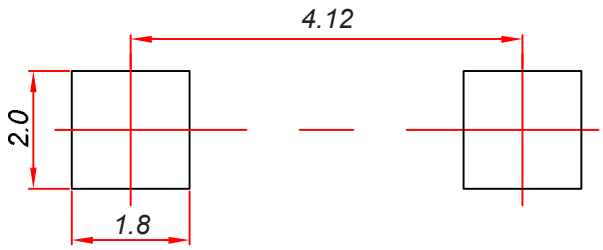


FIG.4：TYPICAL REVERSE CHARACTERISTICS



SMA Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

>>GP(格瑞宝)